

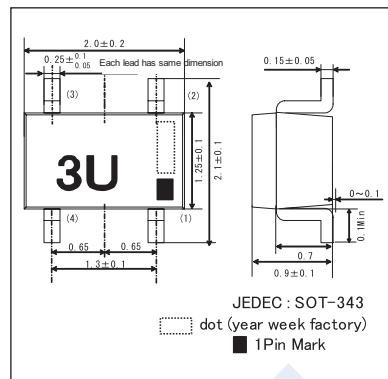
Schottky Diodes

RB481K

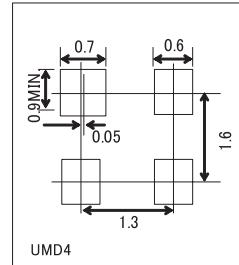
■ Features

- Ultra small mold type.
- LowVF
- High reliability

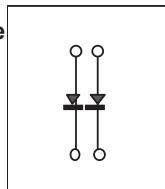
● External dimensions (Unit : mm)



● Land size figure (Unit : mm)



● Structure



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	VRM	30	V
Reverse voltage (DC)	VR	30	
Average rectified forward current (*1)	Io	200	mA
Forward current surge peak (60Hz.1cyc) (*1)	IFSM	1	A
Junction Temperature	TJ	125	°C
Storage Temperature range	Tstg	-40 to +125	

(*1) Rating of per diode

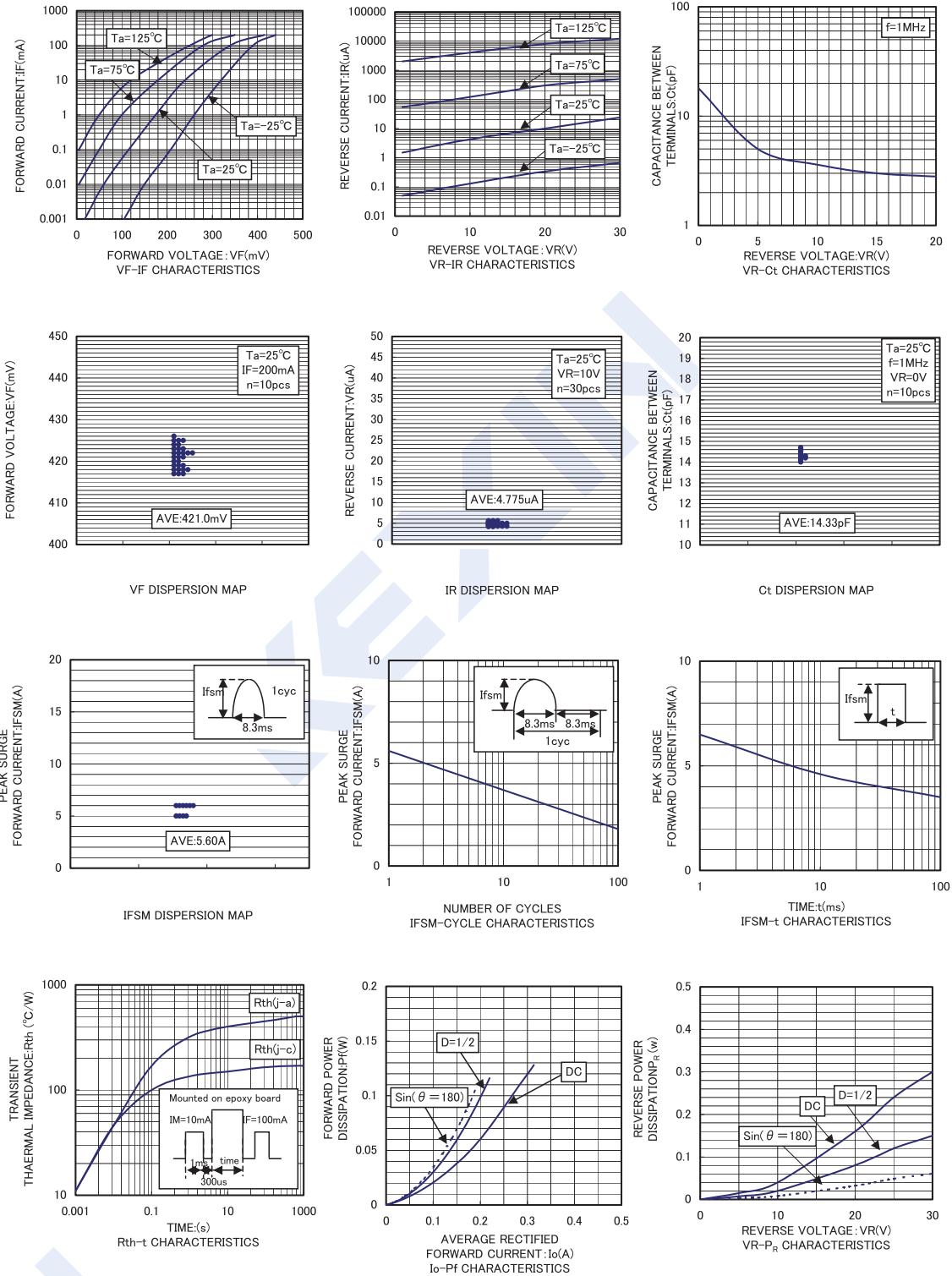
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	VR	IR= 100 μA	30			V
Forward voltage	VF1	IF= 1mA			0.28	
	VF2	IF= 10mA			0.33	
	VF3	IF= 100mA			0.43	
	VF4	IF= 200mA			0.50	
Reverse current	IR	VR= 10 V			30	μA

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■ Electrical characteristic curves ($T_a=25^\circ\text{C}$)



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